

Title (en)

SEMICONDUCTOR ELECTRON EMITTING DEVICE WHOSE ACTIVE LAYER HAS A DOPING GRADIENT

Publication

**EP 0066926 B1 19850213 (FR)**

Application

**EP 82200648 A 19820527**

Priority

FR 8110993 A 19810603

Abstract (en)

[origin: US4518980A] An electron emitting device including an active semiconductor layer having a surface from which electrons are emitted. The layer is doped with impurity atoms at a density which decreases with distance from the surface.

IPC 1-7

**H01J 1/34**; **H01J 1/32**; **H01J 43/10**; **H01J 40/06**

IPC 8 full level

**H01J 1/30** (2006.01); **H01J 1/308** (2006.01); **H01J 1/32** (2006.01); **H01J 1/34** (2006.01)

CPC (source: EP US)

**H01J 1/32** (2013.01 - EP US); **H01J 1/34** (2013.01 - EP US); **H01J 2201/3423** (2013.01 - EP US)

Citation (examination)

- US 3959038 A 19760525 - GUTIERREZ WILLIAM A, et al
- FR 2300413 A1 19760903 - LABO ELECTRONIQUE PHYSIQUE [FR]

Cited by

EP1024513A4; EP0413482A3; GB2170648A; US4677342A; GB2170648B

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

**EP 0066926 A1 19821215**; **EP 0066926 B1 19850213**; DE 3262303 D1 19850328; FR 2507386 A1 19821210; FR 2507386 B1 19840504; JP H0411973 B2 19920303; JP S57210539 A 19821224; US 4518980 A 19850521

DOCDB simple family (application)

**EP 82200648 A 19820527**; DE 3262303 T 19820527; FR 8110993 A 19810603; JP 9227582 A 19820601; US 38063382 A 19820521